Search Notes

			Υ	
L Number	Hits	Search Text	DB	Time stamp
_	0	upstanding adj pillar same etch\$3 and gate and pore	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/15 00:12
_	0	upstanding adj pillar and etch\$3 and gate and pore	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/15
-	224	upstanding adj pillar	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/15 00:12
-	19	upstanding adj pillar and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/15 00:13
-	8	upstanding adj pillar and etch\$3 and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/15
-	17	upstanding with pillar and etch\$3 and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/15 00:15
_	62	pillar and etch\$3 and gate and pore	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/15
-	3	pillar and etch\$3 and gate same pore	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/15
_	5	pillar and gate same pore	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/15 00:32
_	218	channel and gate same pore	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/15 00:33
_	102	channel and gate with pore	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/15
_	5	channel and gate with pore and stack	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/15 00:36
-	69	pore same transistor and channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/11 22:20

-	3	pore same transistor and channel and gate	USPAT;	2004/06/11
		and etch\$3 and pillar	US-PGPUB;	22:41
			EPO; JPO;	
			DERWENT;	
		(430 (360) 661 6	IBM_TDB	2004/06/11
-	555	(438/268).CCLS.	USPAT;	2004/06/11
			US-PGPUB; EPO; JPO;	22:28
			DERWENT;	
			IBM TDB	
_	1684	(438/270).CCLS.	USPAT;	2004/06/11
	1004	(100/10/10010)	US-PGPUB;	22:28
			EPO; JPO;	12.20
			DERWENT;	
			IBM TDB	
-	676	(257/382).CCLS.	USPAT;	2004/06/11
	1		US-PGPUB;	22:28
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	288	(257/383).CCLS.	USPAT;	2004/06/11
			US-PGPUB;	22:28
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	534	(257/302).CCLS.	USPAT;	2004/06/11
			US-PGPUB;	22:28
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	796	(438/197).CCLS.	USPAT;	2004/06/11
			US-PGPUB;	22:34
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	2004/06/22
-	0	nanopillar and transistor and nanppore	USPAT;	2004/06/11
1			US-PGPUB;	22:35
			EPO; JPO;	
			DERWENT; IBM TDB	
_	1	nanopillar and transistor and nanopore	USPAT;	2004/06/11
[*		US-PGPUB;	22:35
			EPO; JPO;	22.33
			DERWENT;	
]			IBM TDB	
_	7	nanopillar and transistor	USPAT;	2004/06/11
]	,		US-PGPUB;	22:37
-			EPO; JPO;]
			DERWENT;	
			IBM TDB	
ļ -	52	pore same transistor and channel and gate	USPAT;	2004/06/11
		and etch\$3	US-PGPUB;	22:41
			EPO; JPO;	[
			DERWENT;	
			IBM_TDB	
-	3		USPAT;	2004/06/11
		and etch\$3 and pillar	US-PGPUB;	22:41
			EPO; JPO;	
			DERWENT;	
			IBM_TDB]